

## REMARKS

### *A. Status of Application*

The Specification has been amended to correct inadvertent typographical errors. No new matter was introduced. Claims 2-4, 8-10, 13, 14, 18, 20, 21, and 24 have been canceled, claims 1, 5, 11, 12, 15, and 22 have been amended, and claim 25 and 26 have been added. Therefore, claims 1, 5-7, 11, 12, 15-17, 19, 22, 23, 25, 26 remain in this application and are presented for reconsideration.

### *B. Section 102 Rejection*

Claims 1-24 stand rejected under 35 U.S.C. § 102(e) as allegedly being anticipated by U.S. Patent No. 6,731,173 to Philip H. Thompson. In light of the above claim amendments and the comments below, Applicants respectfully traverse.

Amended independent claim 1 recites, in pertinent part:

a self-bias Field Effect Transistor integrated on the semiconductor die and coupled to the Doherty amplifier, the self-bias Field Effect Transistor and resistor divide network together biasing the Doherty amplifier

Independent claims 5, 15, and 22 have been amended to recite a similar limitation. Support for the amendments, may be found, for example, in the FIG. 2 and supporting text of the Specification. In one respect, the self-bias Field Effect Transistor may be used to “track variations in device parameters such as threshold voltage ( $V_{th}$ ) or the transconductance ( $g_m$ ) of the peaking amplifier transistor 116. Accordingly, in one embodiment of the present disclosure, biasing of the peaking amplifier transistor is based on the quiescent conditions of reference FET 112.” See FIGs. 1B and 2 and page 6, lines 5-8.

In contrast, this feature is completely absent from Thompson. Referring to FIGs. 1-4 of the Thompson reference, a bias circuit 104 is used to provide a bias voltage to carrier amplifier 110 and peaking amplifier 114. The bias circuit 104 fails to include a self-bias FET integrated on the semiconductor die and coupled to the Doherty amplifier, the self-bias Field Effect Transistor and resistor divide network together biasing the Doherty amplifier 102 as recited in the claims.

Because the Thompson reference lacks disclosure of explicit elements of the claims, it cannot serve as an anticipatory reference. Applicants respectfully request the removal of the § 102 rejection to independent claims 1, 5, 15, and 22, and all their respective dependent claims.

*C. New Claims 25 and 26*

The present paper adds dependent claim 25 and 26 which is directed to a self-bias Field Effect Transistor. Support for claims 25 and 26 may be found, for example, in FIG. 2 and supporting text in the Specification.

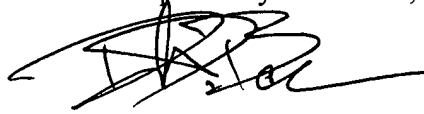
As noted above, the cited reference fails to disclose or render obvious the details of the self-bias Field Effect transistor as recited in claim 1. For at least these reasons, claims 25 and 26 are patentably distinct over the Thompson reference.

### CONCLUSION

Applicants believe the foregoing to be a full and complete response to the subject Office Action, and respectfully request the withdrawal of the rejections to claims, the allowance of claims 1, 5-7, 11, 12, 15-17, 19, 22, 23, 25, 26, and the issuance of a timely Notice of Allowance.

Should the Examiner believe that a personal discussion would be helpful, he is encouraged to contact the undersigned attorney at 512/536-3005 with any questions, comments, or suggestions relating to the referenced patent application.

Respectfully submitted,



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